

RJL6012DPE

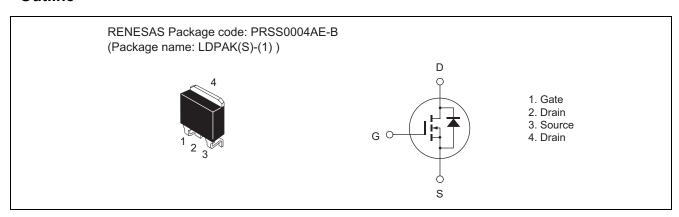
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1750-0100 Rev.1.00 Oct 26, 2009

Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source voltage	V_{DSS}	600	V
Gate to Source voltage	V_{GSS}	±30	V
Drain current	I _D	10	Α
Drain peak current	I _{D (pulse)} Note1	30	Α
Body-Drain diode reverse Drain current	I _{DR}	10	Α
Body-Drain diode reverse Drain peak current	I _{DR (pulse)} Note1	30	Α
Avalanche current	I _{AP} Note3	3	Α
Avalanche energy	E _{AR} Note3	0.49	mJ
Channel dissipation	Pch Note2	100	W
Channel to case thermal impedance	θch-c	1.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

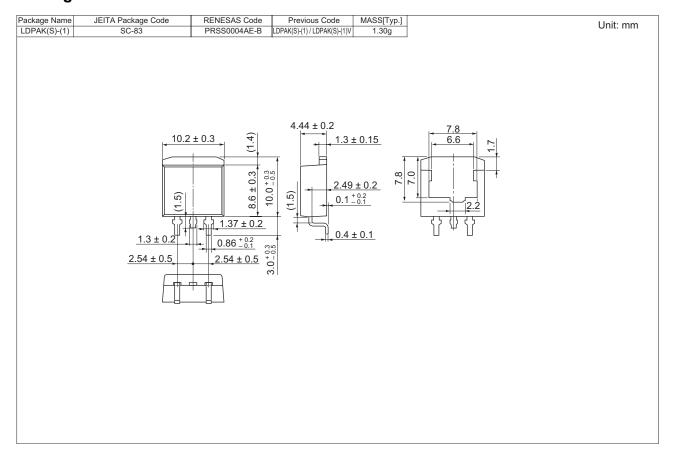
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero Gate voltage drain current	I _{DSS}		_	10	μΑ	V _{DS} = 600 V, V _{GS} = 0
Gate to Source leak current	I _{GSS}		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static Drain to Source on state resistance	R _{DS(on)}	1	0.88	1.10	Ω	I _D = 5 A, V _{GS} = 10 V ^{Note4}
Input capacitance	Ciss		1050	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	105	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	12	_	pF	f = 1 MHz
Turn-on delay time	$t_{d(on)}$	_	27	_	ns	I _D = 5 A
Rise time	t _r	_	20	_	ns	V _{GS} = 10 V
Turn-off delay time	$t_{d(off)}$	_	78	_	ns	$R_L = 60 \Omega$
Fall time	t _f	_	16	_	ns	$Rg = 10 \Omega$
Total Gate charge	Qg	_	28	_	nC	V _{DD} = 480 V
Gate to Source charge	Qgs	_	4.8	_	nC	V _{GS} = 10 V
Gate to Drain charge	Qgd	_	14.2	_	nC	I _D = 10 A
Body-Drain diode forward voltage	V_{DF}	_	1.0	1.7	V	I _F = 10 A, V _{GS} = 0 Note4
Body-Drain diode reverse recovery time	trr		150	_	ns	$I_F = 10 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJL6012DPE-00-J3	1000 pcs	Taping

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